



2020년 2월 14일(금), 15:45~17:30

Room K (다이아몬드 I, 6층)

**D. Thin Film Process Technology 분과**

**[FK3-D] Thin Film Transistors**

<b>FK3-D-1</b> 15:45~16:15	<b>[초청]</b> <b>Geometrically Adaptive Atomically Thin Films</b> Joonki Suh <i>School of Materials Science and Engineering, UNIST</i>
<b>FK3-D-2</b> 16:15~16:30	<b>용액 공정 기반의 이중 게이트 전극 구조의 산화물 Indium-gallium-zinc-oxide TFT의 제작 및 분석</b> Jeongmin Kim and Jaewook Jeong <i>School of Information and Communication Engineering, Chungbuk National University</i>
<b>FK3-D-3</b> 16:30~16:45	<b>High-Performance ZnO-based Thin Film Transistors with Thin ITO Inserting Layers Suitable for Low Temperature Processing</b> Man-ho Cho and Won-Ju Cho <i>Department of Electronic Materials Engineering, Kwangwoon University</i>
<b>FK3-D-4</b> 16:45~17:00	<b>Mechanically Flexible Vertical-Channel Charge-Trap Memory Thin Film Transistors Using Atomic Layer Deposited Oxide Semiconductors</b> Hyeong-Rae Kim and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
<b>FK3-D-5</b> 17:00~17:15	<b>Fabrication and Characterization of Nanoscale In-Ga-Zn-O Vertical-Channel Thin-Film-Transistors with Sub-130 nm Channel Length</b> Hyun-Joo Ryoo and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
<b>FK3-D-6</b> 17:15~17:30	<b>Annealing Effect on IGZO-Metal Interface</b> Eun Seong Yu, Seok Jun Kang, Jae Geun Woo, In Hye Kang, and Byung Seong Bae <i>School of Electronics and Display Engineering, Hoseo University</i>